

PMV30XPEAR-VB Datasheet

Single-P SOT23-3 Trench -20V MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 20
$R_{DS(on)}$ (Ω) at $V_{GS} = - 4.5$ V	0.034
$R_{DS(on)}$ (Ω) at $V_{GS} = - 2.5$ V	0.046
$R_{DS(on)}$ (Ω) at $V_{GS} = - 1.8$ V	0.067
I_D (A)	- 5
Configuration	Single

FEATURES

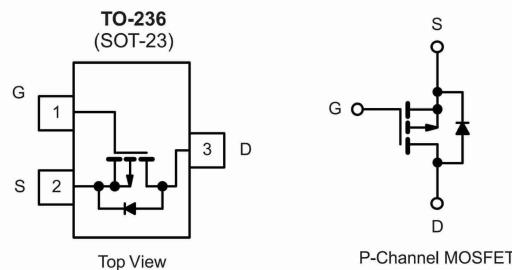
- Halogen-free Option Available
- TrenchFET® Power MOSFET



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch for Portable Devices



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 20	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current	$T_C = 25$ °C	I_D	- 5	A
	$T_C = 125$ °C		- 3	
Continuous Source Current (Diode Conduction)		I_S	- 2.5	
Pulsed Drain Current ^a		I_{DM}	- 20	
Single Pulse Avalanche Current	$L = 0.1$ mH	I_{AS}	- 11	mJ
Single Pulse Avalanche Energy		E_{AS}	6	
Maximum Power Dissipation ^a	$T_C = 25$ °C	P_D	2	
	$T_C = 125$ °C		0.67	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

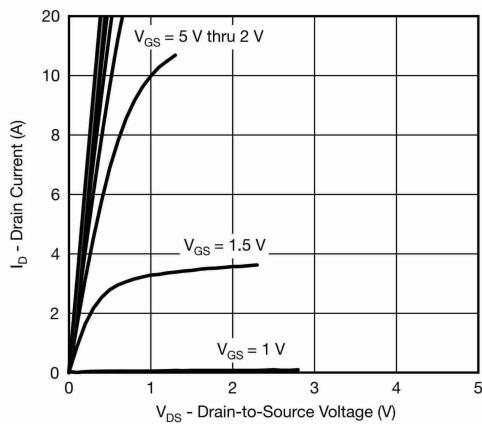
THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R_{thJA}	175	°C/W
Junction-to-Foot (Drain)		R_{thJF}	75	

SPECIFICATIONS ($T_C = 25^\circ\text{C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$		- 20	-	-	V	
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$		- 0.45	-	- 1		
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 8\text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = -12\text{ V}$	-	-	- 1	μA	
		$V_{GS} = 0\text{ V}$	$V_{DS} = -12\text{ V}$, $T_J = 125^\circ\text{C}$	-	-	- 50		
		$V_{GS} = 0\text{ V}$	$V_{DS} = -12\text{ V}$, $T_J = 175^\circ\text{C}$	-	-	- 150		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{GS} = -4.5\text{ V}$	$V_{DS} \leq -5\text{ V}$	- 10	-	-	A	
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -4.5\text{ V}$	$I_D = -3.5\text{ A}$	-	0.034	-	Ω	
		$V_{GS} = -4.5\text{ V}$	$I_D = -3.5\text{ A}$, $T_J = 125^\circ\text{C}$	-	0.066	-		
		$V_{GS} = -4.5\text{ V}$	$I_D = -3.5\text{ A}$, $T_J = 175^\circ\text{C}$	-	0.075	-		
		$V_{GS} = -2.5\text{ V}$	$I_D = -3\text{ A}$	-	0.046	-		
		$V_{GS} = -1.8\text{ V}$	$I_D = -2\text{ A}$	-	0.067	-		
Forward Transconductance ^b	g_{fs}	$V_{DS} = -5\text{ V}$, $I_D = -1.6\text{ A}$		-	7	-	S	
Dynamic^b								
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = -6\text{ V}$, $f = 1\text{ MHz}$	-	695	870	pF	
Output Capacitance	C_{oss}			-	265	335		
Reverse Transfer Capacitance	C_{rss}			-	190	240		
Total Gate Charge ^c	Q_g	$V_{GS} = -4.5\text{ V}$	$V_{DS} = -6\text{ V}$, $I_D = -3.85\text{ A}$	-	8.4	13	nC	
Gate-Source Charge ^c	Q_{gs}			-	1	-		
Gate-Drain Charge ^c	Q_{gd}			-	2.4	-		
Gate Resistance	R_g	$f = 1\text{ MHz}$		4.1	8.2	12.3	Ω	
Turn-On Delay Time ^c	$t_{d(\text{on})}$	$V_{DD} = -6\text{ V}$, $R_L = 1.6\text{ }\Omega$ $I_D \cong -3.85\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 1\text{ }\Omega$		-	17	26	ns	
Rise Time ^c	t_r			-	19	29		
Turn-Off Delay Time ^c	$t_{d(\text{off})}$			-	28	42		
Fall Time ^c	t_f			-	13	20		
Source-Drain Diode Ratings and Characteristics^b								
Pulsed Current ^a	I_{SM}			-	-	- 20	A	
Forward Voltage	V_{SD}	$I_F = -2\text{ A}$, $V_{GS} = 0\text{ V}$		-	- 0.8	- 1.2	V	

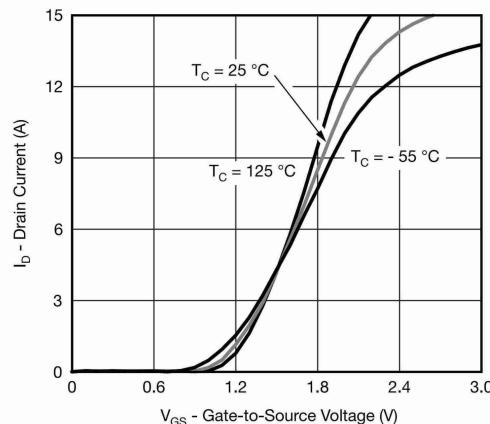
Notes

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\text{ \%}$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

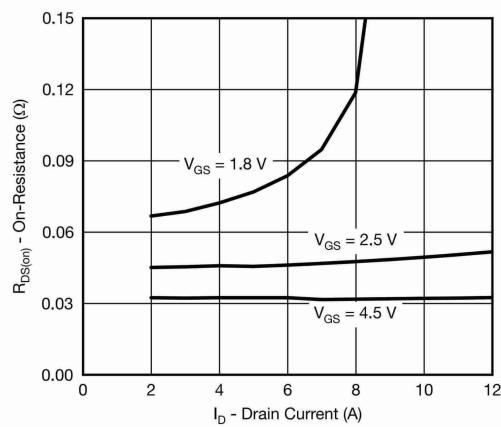
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)


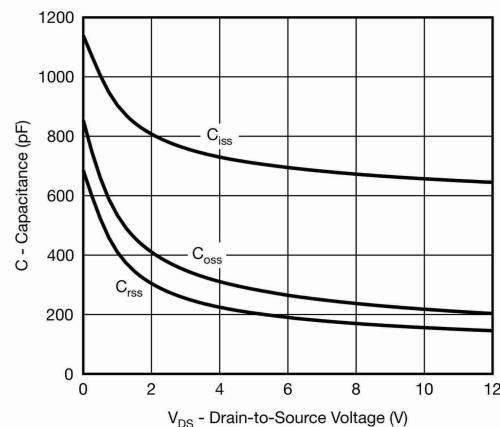
Output Characteristics



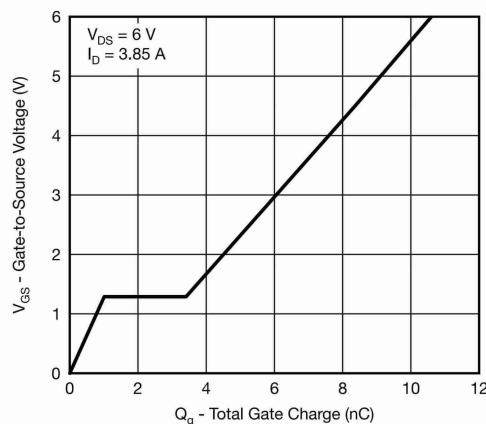
Transfer Characteristics



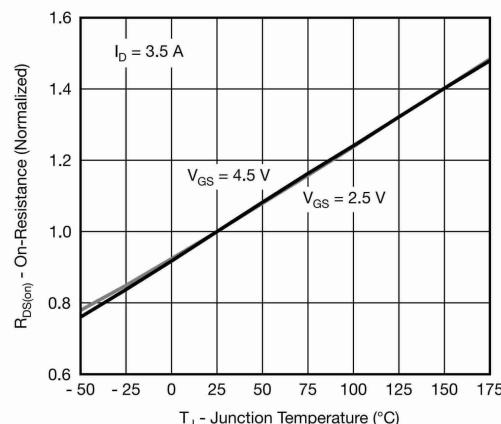
On-Resistance vs. Drain Current



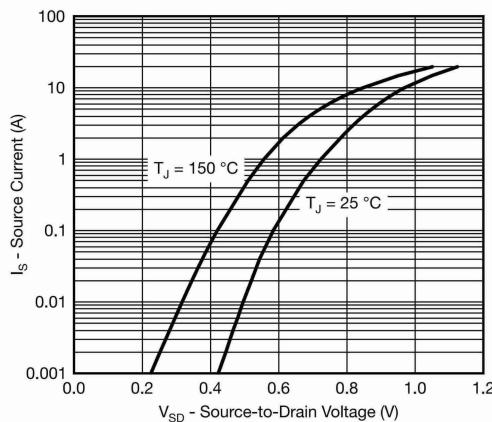
Capacitance



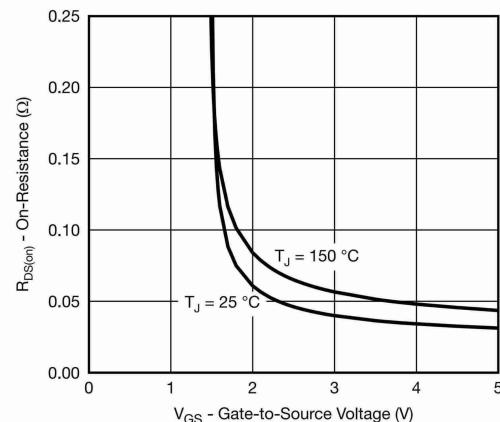
Gate Charge



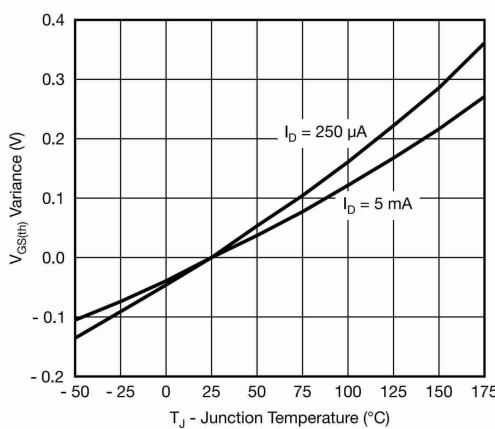
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)


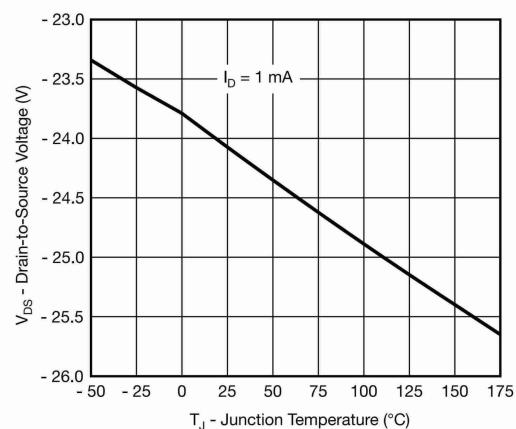
Source-Drain Diode Forward Voltage



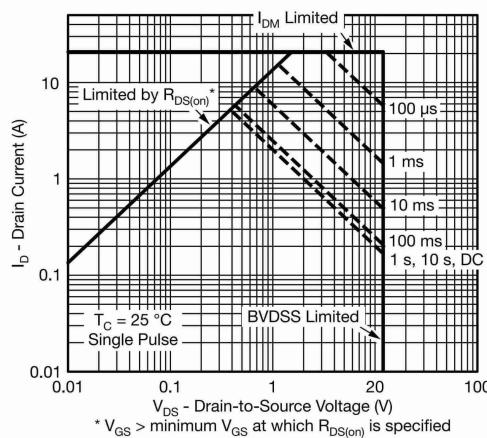
On-Resistance vs. Gate-to-Source Voltage



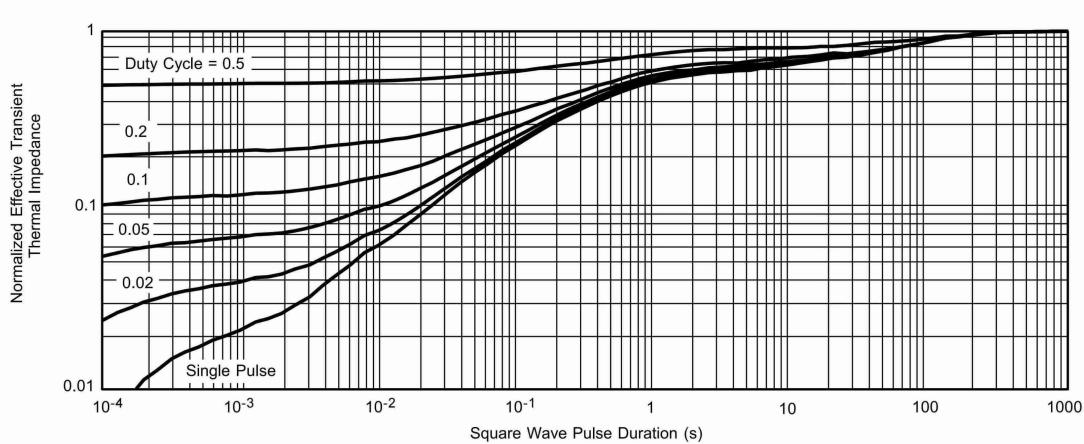
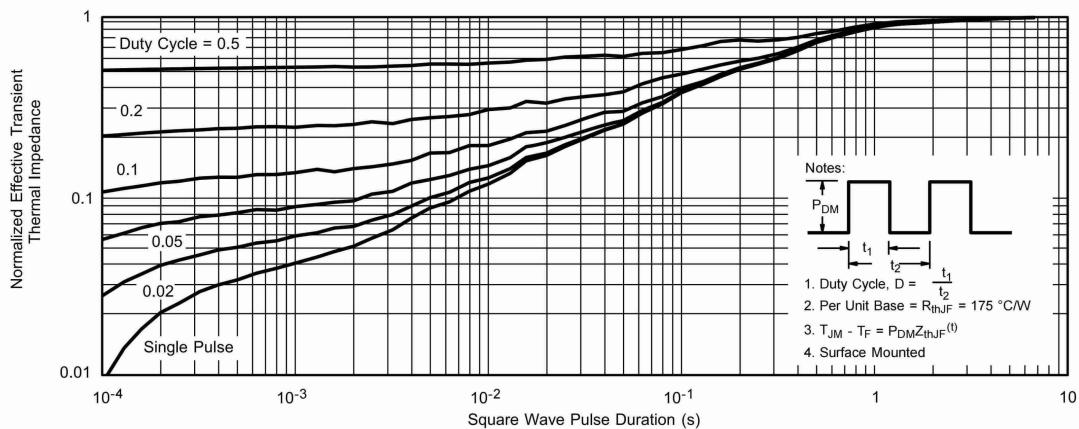
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

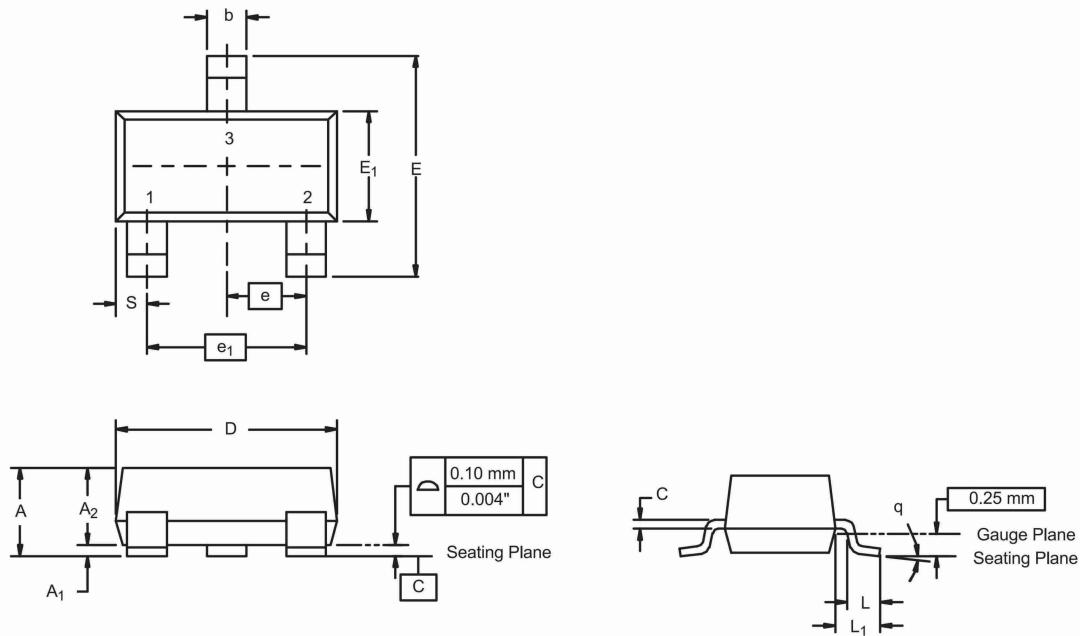


Safe Operating Area

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)**Note**

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25°C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25°C)

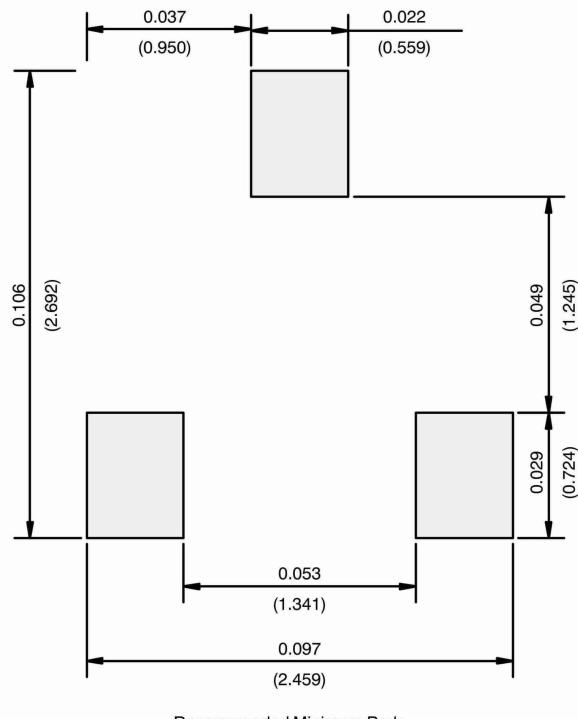
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-23 (TO-236): 3-LEAD

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A₁	0.01	0.10	0.0004	0.004
A₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

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 DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23

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